L	Hits	Search Text	DB	Time stamp
Number	1050		WCD2 W.	2004/06/17
2	1952	(gate with oxide) same polysilicon same silicide same nitride	USPAT; US-PGPUB	2004/06/17 14:54
3	1144	(gate adj oxide) same polysilicon same	USPAT;	2004/06/17
Ĭ	1111	silicide same nitride	US-PGPUB	14:55
5	58	((gate adj oxide) same polysilicon same	USPAT;	2004/06/17
		silicide same nitride) and ((spacers with	US-PGPUB	14:56
		oxide) same temperature)		
6	,57	(((gate adj oxide) same polysilicon same	USPAT;	2004/06/17
		silicide same nitride) and ((spacers with	US-PGPUB	17:08
		oxide) same temperature)) and		
10	278	@ad<20021031	HCDNM.	2004/06/17
10	2/0	gate and (oxidizing same spacers same oxide) and @ad<20021031	USPAT; US-PGPUB	15:13
11	3	(gate and (oxidizing same spacers same	USPAT;	2004/06/17
**	_	oxide) and @ad<20021031) and (oxygen same	US-PGPUB	17:08
		inert same oxidizing) and @ad<20021031		
12	1379	gate and ((thermal or rapid) same spacers	USPAT;	2004/06/17
		same oxide) and @ad<20021031	US-PGPUB	15:13
13	14	(gate and ((thermal or rapid) same	USPAT;	2004/06/17
		spacers same oxide) and @ad<20021031) and	US-PGPUB	15:14
		(oxygen same inert same (thermal or		
14	2019	rapid)) and @ad<20021031 gate with oxide with polysilicon with	USPAT;	2004/06/17
7.3	2019	silicide	US-PGPUB	17:39
15	8	(gate with oxide with polysilicon with	USPAT;	2004/06/17
		silicide) same sidewall same (thermal or	US-PGPUB	17:06
		thermally or rapid or oxidize or		
,		oxidizing or oxidation) same (inert or		
	_	argon or nitrogen)		
16	7	((gate with oxide with polysilicon with	USPAT;	2004/06/17
		silicide) same sidewall same (thermal or	US-PGPUB	17:07
		thermally or rapid or oxidize or oxidizing or oxidation) same (inert or		
		argon or nitrogen)) and @ad<20021031		
17	265	(gate with oxide with polysilicon with	USPAT;	2004/06/17
- '		silicide) and (sidewall or spacers) and	US-PGPUB	17:40
		((thermal or thermally or rapid or		
		oxidize or oxidizing or oxidation) same		
	0.47	(inert or argon or nitrogen))	***************************************	2004/06/17
18	247	((gate with oxide with polysilicon with silicide) and (sidewall or spacers) and	USPAT; US-PGPUB	2004/06/17
		((thermal or thermally or rapid or	05-16105	17.07
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen))) and		
		@ad<20021031		
19	240	(((gate with oxide with polysilicon with	USPAT;	2004/06/17
		silicide) and (sidewall or spacers) and	US-PGPUB	17:08
		((thermal or thermally or rapid or oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen))) and		
		(life to of algorithm of mittogen,), and (ead<20021031) not ((gate with oxide with		
		polysilicon with silicide) same sidewall		
		same (thermal or thermally or rapid or		
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen)) and		
20	232	<pre>@ad<20021031) ((((gate with oxide with polysilicon with</pre>	USPAT;	2004/06/17
20	232	((((gate with oxide with polysilicon with silicide) and (sidewall or spacers) and	US-PGPUB	17:08
		((thermal or thermally or rapid or	JU TOTOB	1 - 7 - 3 3
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen))) and		
	1	@ad<20021031) not (((gate with oxide with		
	1	polysilicon with silicide) same sidewall		
	1	same (thermal or thermally or rapid or		
	1	oxidize or oxidizing or oxidation) same		
	1	(inert or argon or nitrogen)) and @ad<20021031)) not ((((gate adj oxide)		
	1	same polysilicon same silicide same	1	1
		nitride) and ((spacers with oxide) same		
		temperature)) and @ad<20021031)	<u></u>	

		. , , , , ,		0004/06/25
21	232	(((((gate with oxide with polysilicon	USPAT;	2004/06/17
		with silicide) and (sidewall or spacers) and ((thermal or thermally or rapid or	US-PGPUB	17:08
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen))) and		
		@ad<20021031) not (((gate with oxide with		
		polysilicon with silicide) same sidewall		
		same (thermal or thermally or rapid or		:
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen)) and		
		@ad<20021031)) not ((((gate adj oxide)		
		same polysilicon same silicide same nitride) and ((spacers with oxide) same		
		temperature)) and @ad<20021031)) not		
		((gate and (oxidizing same spacers same		
		oxide) and @ad<20021031) and (oxygen same		
		inert same oxidizing) and @ad<20021031)		
22	232	<pre>((((((gate with oxide with polysilicon</pre>	USPAT;	2004/06/17
		with silicide) and (sidewall or spacers)	US-PGPUB	17:09
		and ((thermal or thermally or rapid or		
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen))) and		
		<pre>@ad<20021031) not (((gate with oxide with polysilicon with silicide) same sidewall</pre>		
		same (thermal or thermally or rapid or		
		oxidize or oxidizing or oxidation) same		
		(inert or argon or nitrogen)) and		
		@ad<20021031)) not ((((gate adj oxide)		
		same polysilicon same silicide same		
		nitride) and ((spacers with oxide) same		
		temperature)) and @ad<20021031)) not ((gate and (oxidizing same spacers same		
		oxide) and @ad<20021031) and (oxygen same		
		inert same oxidizing) and @ad<20021031))		
	l	not ((gate and ((thermal or rapid) same		
	l	spacers same oxide) and @ad<20021031) and		
	l	(oxygen same inert same (thermal or		
	[rapid)) and @ad<20021031)	***************************************	2004/06/17
23	59	(((((((gate with oxide with polysilicon	USPAT; US-PGPUB	2004/06/17 17:10
		with silicide) and (sidewall or spacers) and ((thermal or thermally or rapid or	05-FGF0D	17.10
	ļ	oxidize or oxidizing or oxidation) same		
	,	(inert or argon or nitrogen))) and		
		@ad<20021031) not (((gate with oxide with		
		polysilicon with silicide) same sidewall		
		same (thermal or thermally or rapid or		
		oxidize or oxidizing or oxidation) same (inert or argon or nitrogen)) and		
		(Inert of argon of hitrogen); and @ad<20021031)) not (((gate adj oxide)		
		same polysilicon same silicide same	1	
		nitride) and ((spacers with oxide) same		
		temperature)) and @ad<20021031)) not		
		((gate and (oxidizing same spacers same		
		oxide) and @ad<20021031) and (oxygen same		
		inert same oxidizing) and @ad<20021031)) not ((gate and ((thermal or rapid) same		
		spacers same oxide) and Gad<20021031) and		
	1	(oxygen same inert same (thermal or		
	1	rapid)) and @ad<20021031)) and (oxygen		
		with (inert or argon or nitrogen))		
24	622	gate with oxide with polysilicon with	EPO; JPO;	2004/06/17
	[silicide	DERWENT;	17:39
25	11	(gate with oxide with polysilicon with	IBM_TDB EPO; JPO;	2004/06/17
23	"	silicide) and (sidewall or spacers) and	DERWENT;	17:40
		((thermal or thermally or rapid or	IBM TDB	
		oxidize or oxidizing or oxidation) same		
1		(inert or argon or nitrogen))		